

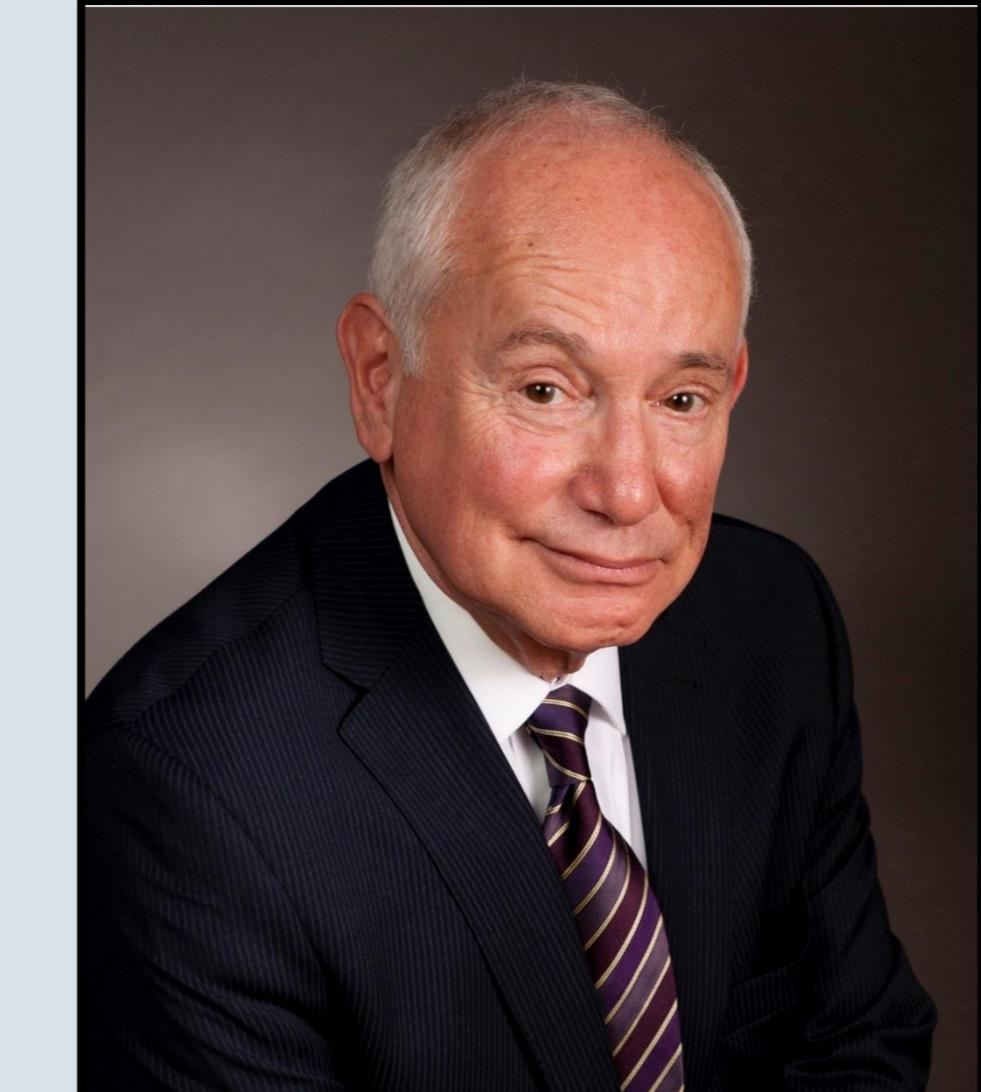
## Discover - Understand - Apply - Prototype



Anu AGARWAL  
Principal Research Scientist  
MIT Microphotronics Center



Jürgen MICHEL  
Senior Research Scientist  
MIT Microphotronics Center



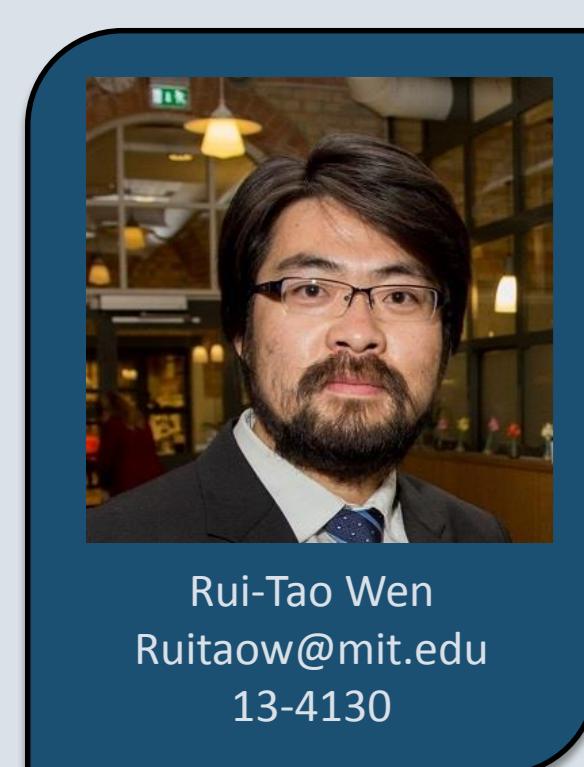
Lionel C. KIMERLING  
Thomas Lord Professor of Materials Science and Engineering  
Director, MIT Microphotronics Center



Xiaoman DUAN  
Research Scientist  
MIT Microphotronics Center

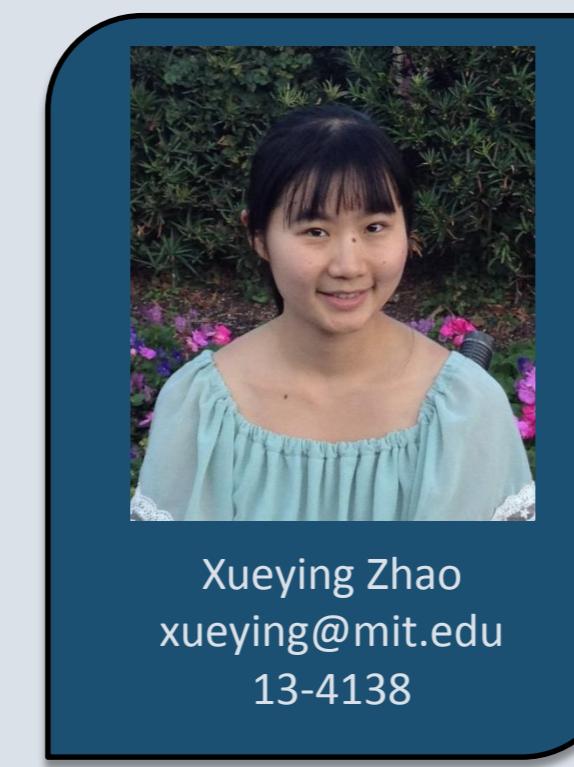


Cory JAMES  
Administrative Assistant  
to Prof. Lionel C. Kimerling



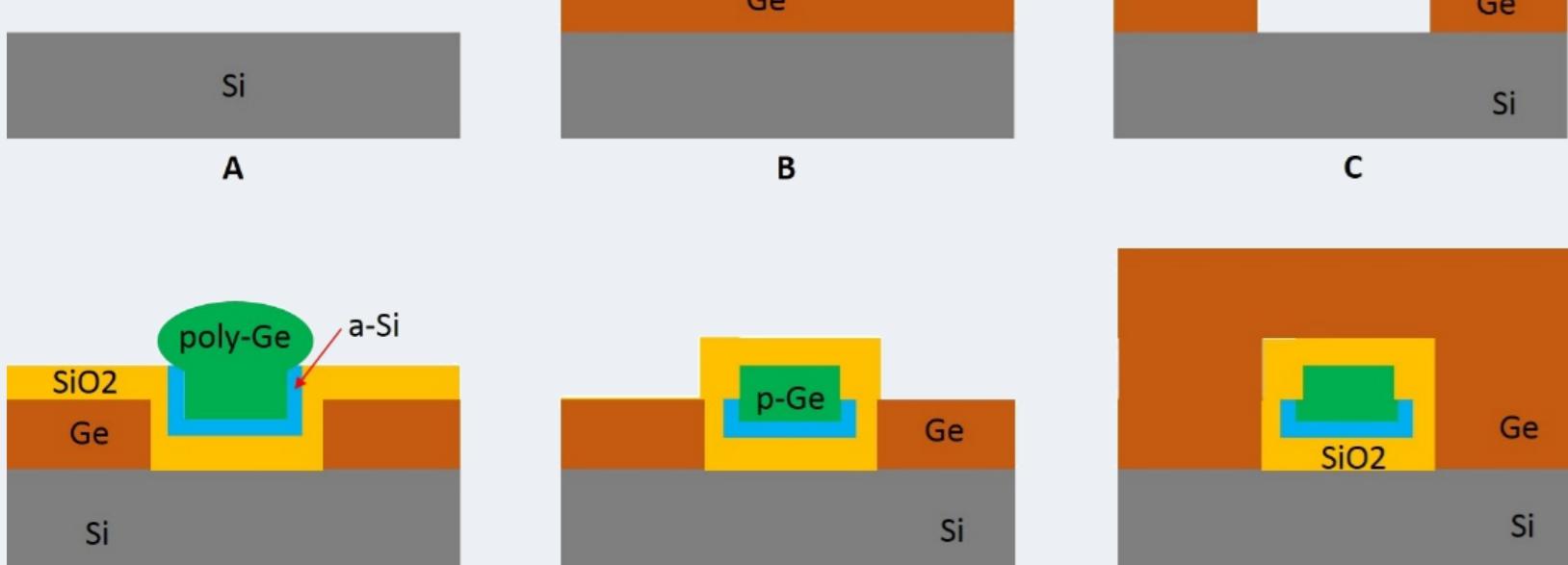
### Integrated Micro-optical Concentrator Photovoltaics with Lateral Multijunction Cells

Achieve high quality Ge on Si wafers for photovoltaics applications

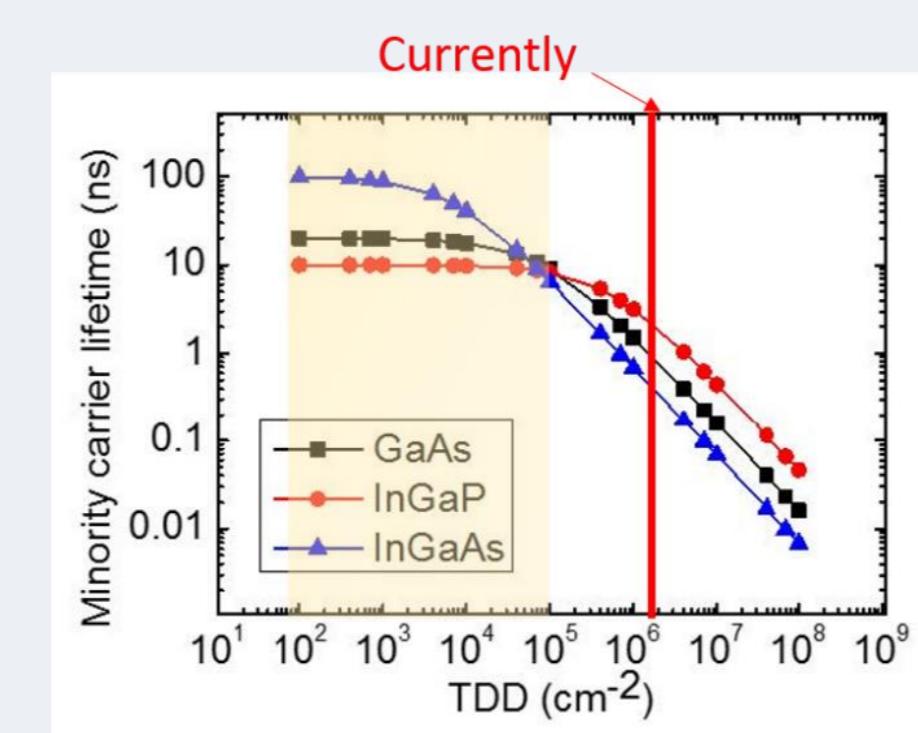


Xueying Zhao  
xueying@mit.edu  
13-4138

- Performance of III-V solar cells is strongly related to the quality of Ge-on-Si substrates. The threading dislocation in Ge layers will be minimized from the optimization of Ge epitaxial growth.
- The same thermal expansion coefficient between Ge and poly-Ge allow threading dislocations move and penetrate during cycling annealing.
- A second epitaxy growth (based on the structure of step E) will yield Ge thin film with very low TDDs.

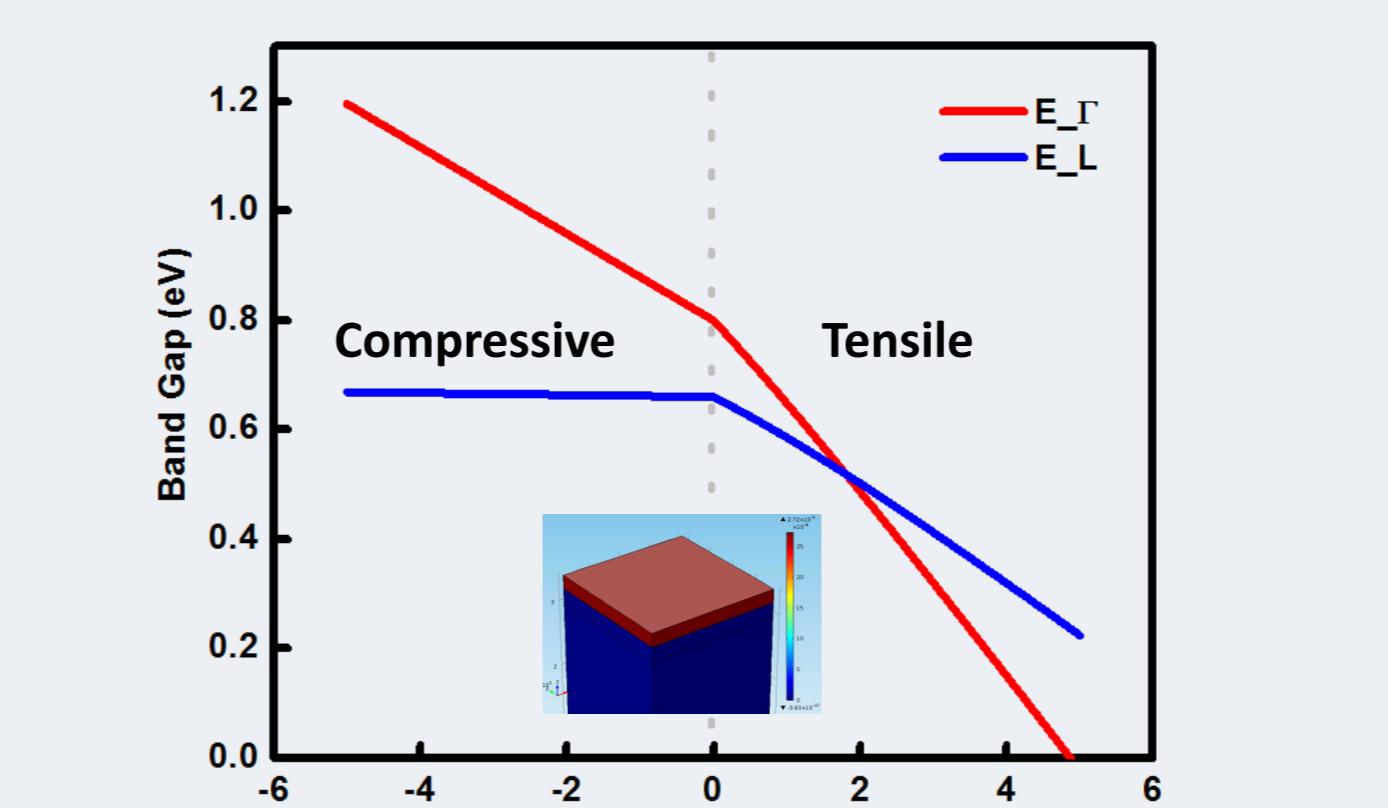
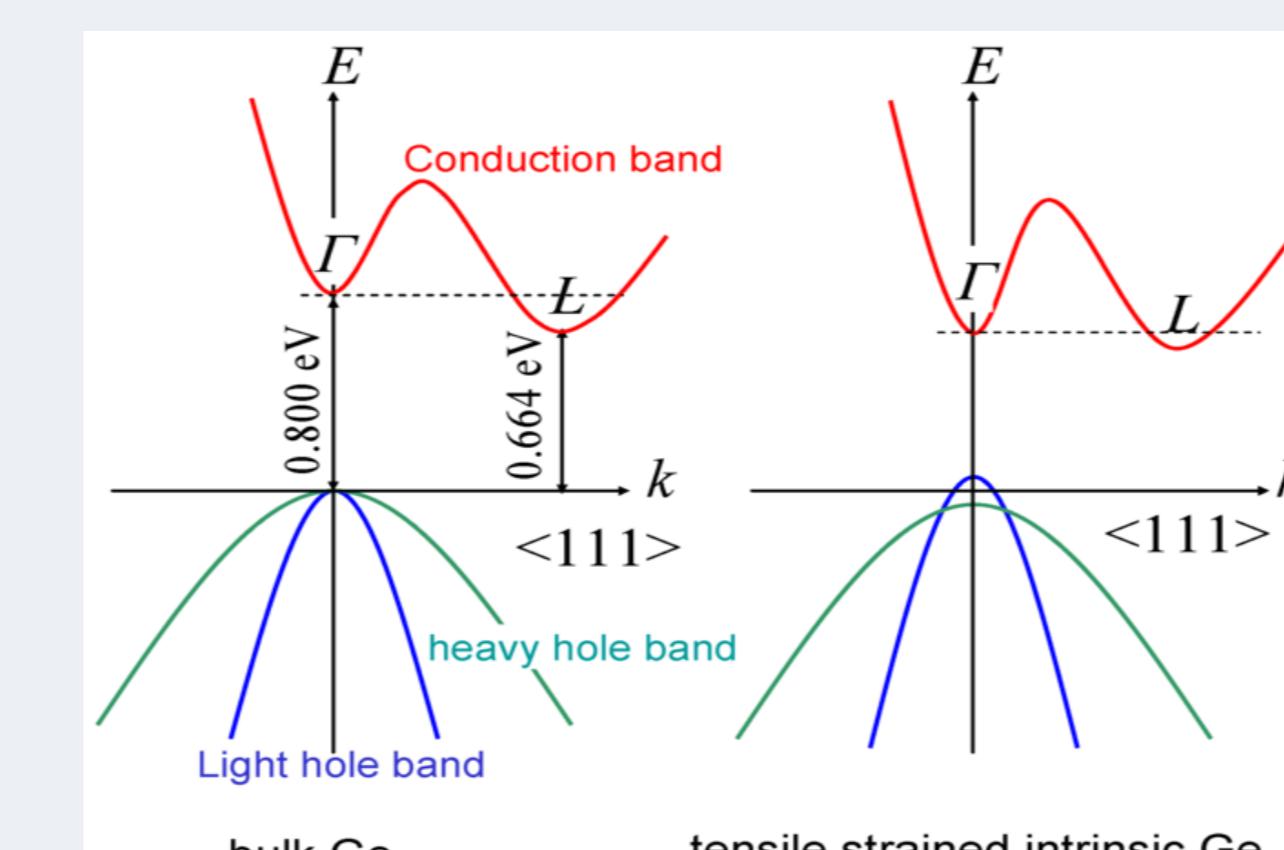


General approach to achieve very low TDD of Ge on Si wafers



Minority carrier lifetimes dependence on TDDs for III-V solar cells

- Grow epitaxial Ge with small amounts of Si
- Electro-absorption modulator fabrication process development
- Realize a scalable integrated quantum photonic interconnect



Band gap of Ge as a function of biaxial strain

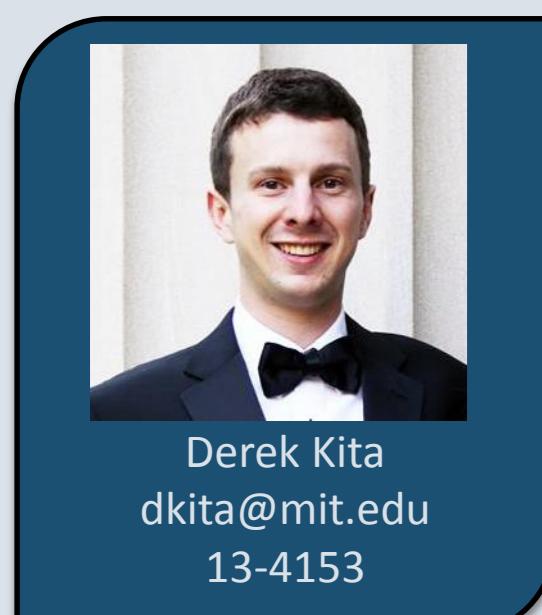


Schematic of UHV CVD Ge film growth

\* Dimensions of the layers are not corresponded.



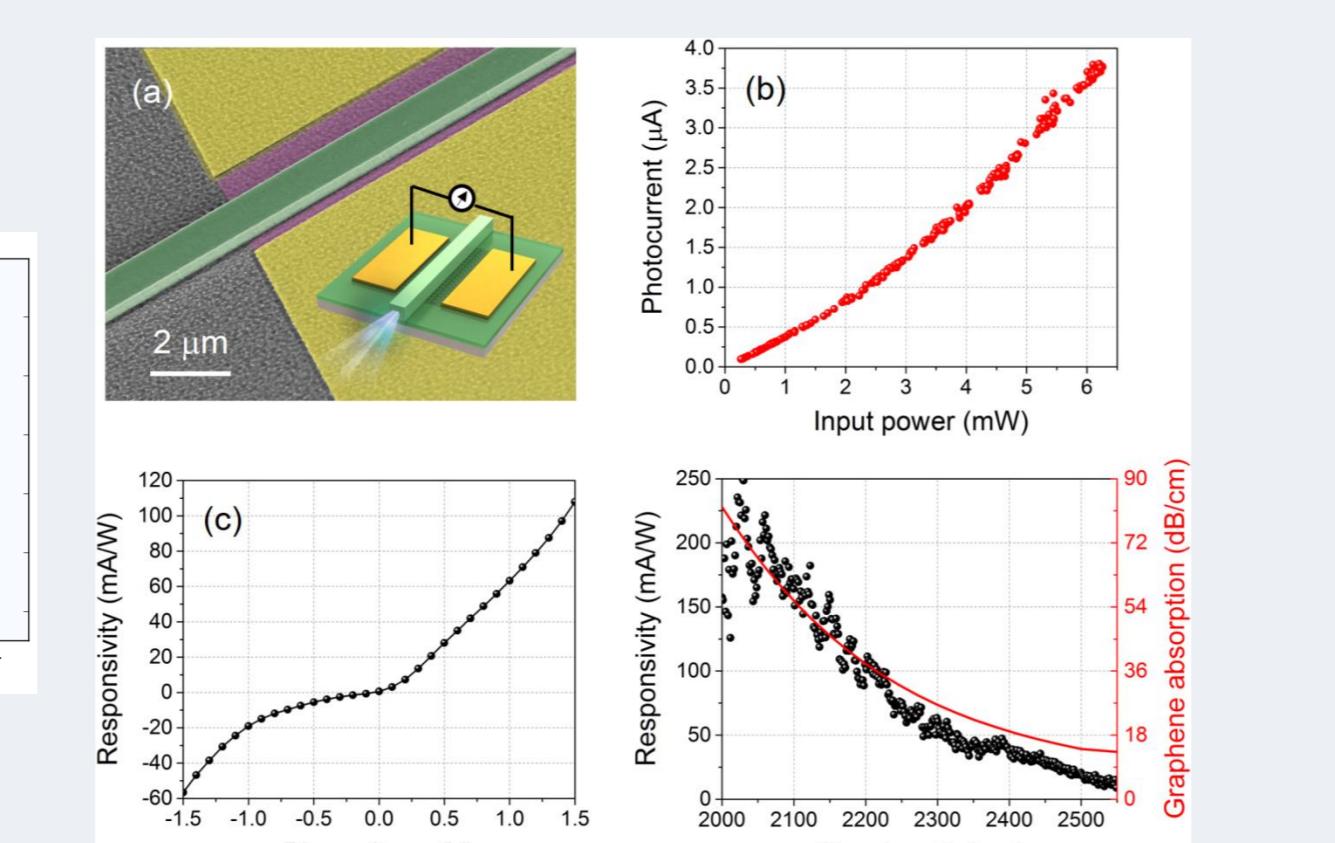
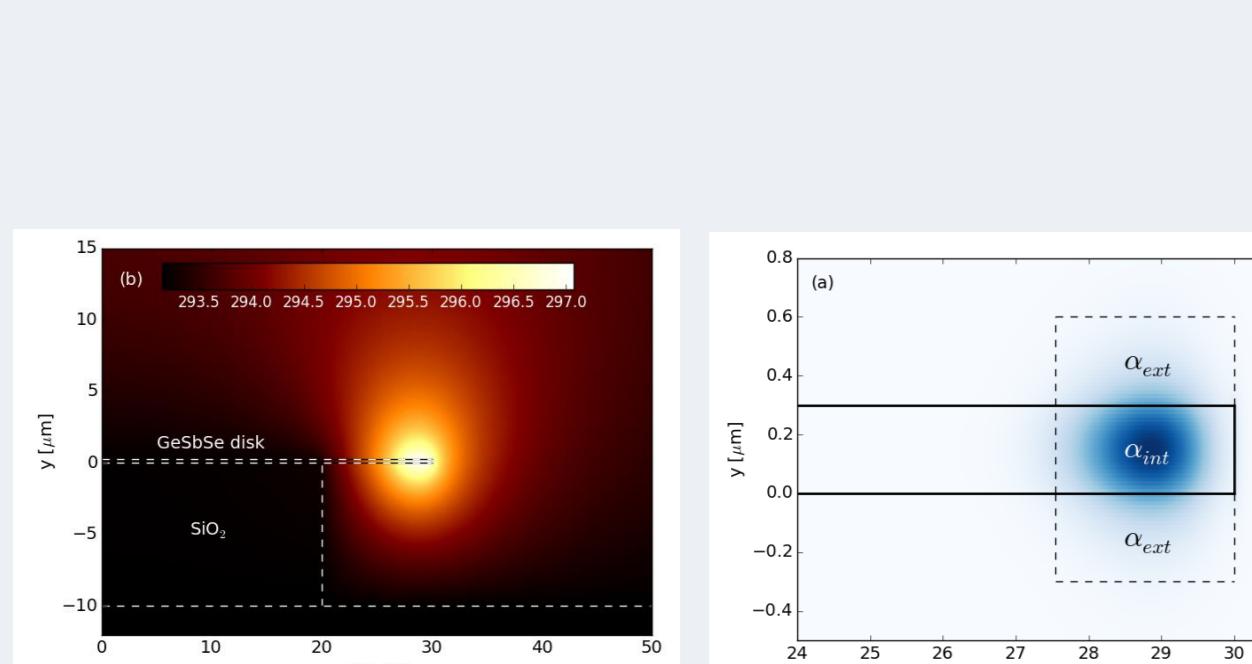
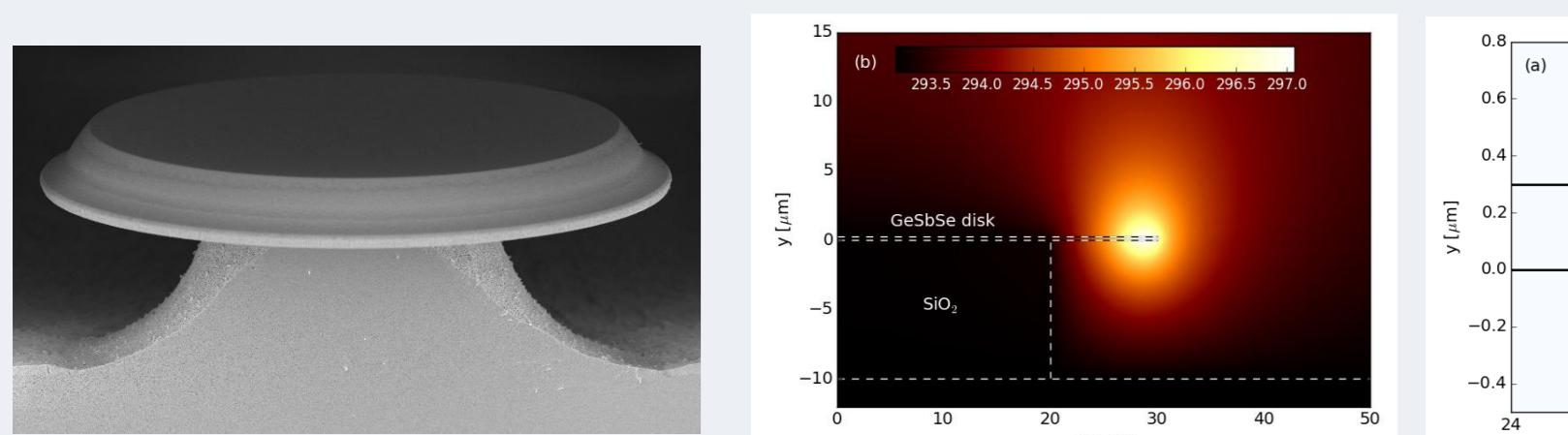
Specular Ge film surface and TEM image of threading dislocations in Ge on Si system



### High-performance Mid-Infrared Photonic Devices for Sensing

Design, simulation, fabrication, and testing of unique photonic materials and device architectures for high-performance spectroscopy in the mid-infrared

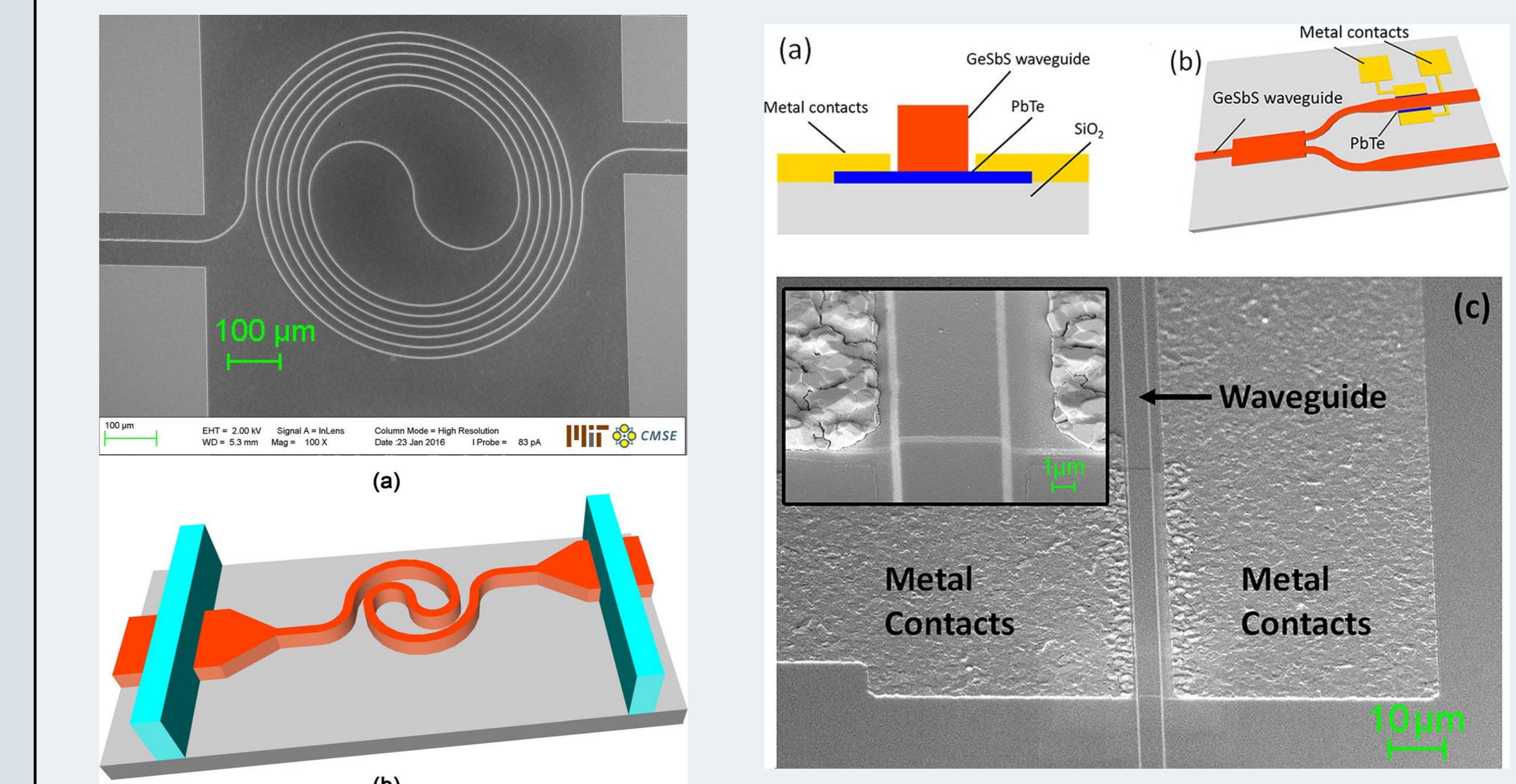
- Suspended chalcogenide microdisk structures for ultra-sensitive photothermal spectroscopy
- Mid-infrared modulators and detectors utilizing PbTe and 2D materials integrated with chalcogenide glass photonics



#### Selected Recent Publications

- Z. Han, V. Singh, D. Kita, C. Monneyran, P. Becla, P. Su, J. Li, X. Huang, L. C. Kimerling, J. Hu, K. Richardson, D. T. H. Tan, and A. Agarwal, *Applied Physics Letters* **109**, 071111 (2016)  
 Z. Han, P. Lin, V. Singh, L. Kimerling, J. Hu, K. Richardson, A. Agarwal, and D. T. H. Tan, *Applied Physics Letters* **108**, 141106 (2016)  
 N. S. Patel, C. Monneyran, A. Agarwal, and L. C. Kimerling, *Journal of Applied Physics* **118**, 155702 (2015).  
 C. Bao, L. Zhang, L. C. Kimerling, J. Michel, and C. Yan, *Optics Express* **23**, 18665 (2015).  
 P. T. Lin, J. Giamarco, N. Borodinov, M. Savchak, V. Singh, L. C. Kimerling, D. T. H. Tan, K. A. Richardson, I. Luzinov, and A. Agarwal, *ACS Appl. Mater. Interfaces* **7**, 11189 (2015).  
 C. Bao, C. Yang, L. Zhang, L. C. Kimerling, and J. Michel, in *CLEO: 2015*, OSA Technical Digest (Optical Society of America, 2015), paper JTu5A.40.  
 D. T. H. Tan, A. M. Agarwal, and L. C. Kimerling, *Laser & Photonics Reviews* **9**, 294 (2015).  
 Z. H. Han, L. Zhang, L. C. Kimerling, and A. M. Agarwal, *IEEE Journal of Selected Topics in Quantum Electronics* **21**, 1603007 (2015).  
 L. Z. Broderick, B. R. Albert, B. S. Pearson, L. C. Kimerling, and J. Michel, *Solar Energy Materials & Solar Cells* **136**, 48 (2015).

- On-chip polycrystalline PbTe photoconductive detector integrated with a chalcogenide glass waveguide
- On-chip sensor for room-temperature detection of methane gas using a broadband spiral chalcogenide glass waveguide coupled with off-chip laser and detector



On-chip sensor for room-temperature detection of methane: (a) single-mode spiral waveguide. (b) schematic representation of the waveguide design

Chalcogenide glass waveguide integrated PbTe photoconductive detector: (a) schematic cross-sectional view of the integrated MIR detector (not to scale). (b) representation of the chip design. (c) A 45° view SEM image of the device.